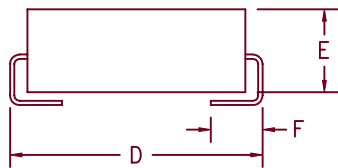
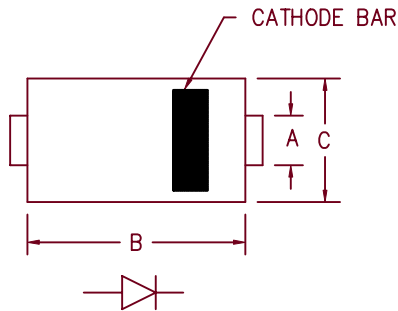


# 1 Amp Ultra Low Forward Voltage Schottky Diode LSM115J



Dim.	Inches		Millimeter		Notes
	Minimum	Maximum	Minimum	Maximum	
A	.073	.087	1.85	2.21	
B	.160	.180	4.06	4.57	
C	.130	.155	3.30	3.94	
D	.205	.220	5.21	5.59	
E	.075	.130	1.91	3.30	
F	.030	.060	.760	1.52	

## D0-214BA Package

Microsemi Catalog Number	Working Peak Reverse Voltage	Repetitive Peak Reverse Voltage
LSM115J	15V	15V

- Schottky Barrier Rectifier
- Guard Ring For Reverse Protection
- Low Power Loss, High Efficiency
- 100°C Junction Temperature
- VRRM 15V
- High Surge Capability
- Ultra Low Forward Voltage
- Schottky OR'ing diode

### Electrical Characteristics

Average forward current	$I_F(AV)$ 1 Amps	$T_L = 65^\circ C$ , Square wave, $R_{\theta JL} = 15^\circ C/W$
Maximum surge current	$I_{FSM}$ 50 Amps	8.3ms, half sine, $T_J = 100^\circ C$
Maximum peak forward voltage	$V_{FM}$ 0.29 Volts	$I_{FM} = 1.0A$ ; $T_J = 25^\circ C^*$
Maximum peak reverse current	$I_{RM}$ 500 mA	$V_{RRM} = 15V$ , $T_J = 100^\circ C$
Maximum peak reverse current	$I_{RM}$ 200 mA	$V_R = 5V$ , $T_J = 100^\circ C$
Maximum peak reverse current	$I_{RM}$ 100 mA	$V_R = 3.3V$ , $T_J = 100^\circ C$
Maximum peak reverse current	$I_{RM}$ 10 mA	$V_{RRM} = 15V$ , $T_J = 25^\circ C$
Typical junction capacitance	$C_J$ 120pF	$T_J = 25^\circ C$ , $V_R = 5V$

\*Pulse test: Pulse width 300  $\mu$ sec. Duty cycle 2%

### Thermal and Mechanical Characteristics

Storage temperature range	$T_{STG}$	$-55^\circ C$ to $150^\circ C$
Operating junction temp range	$T_J$	$-55^\circ C$ to $100^\circ C$
Maximum thermal resistance	$R_{\theta JL}$	$15^\circ C/W$ Junction to Lead
Weight		.0047 ounces (.013 grams) typical

4-3-00 Rev. 2

# LSM115J

Figure 1  
Typical Forward Characteristics

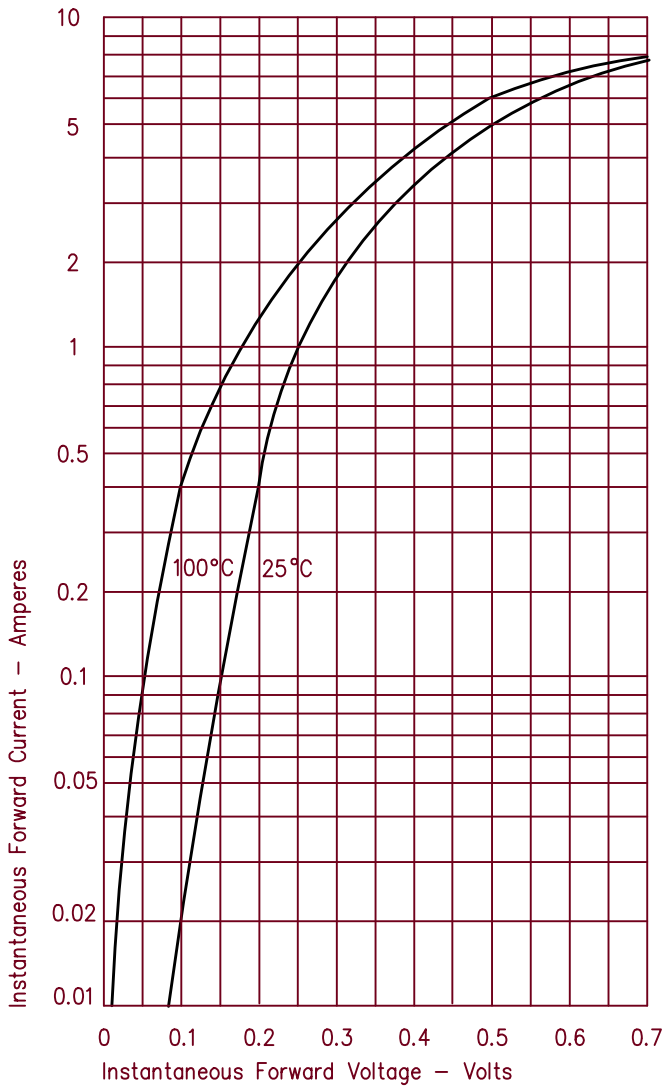


Figure 3  
Typical Junction Capacitance

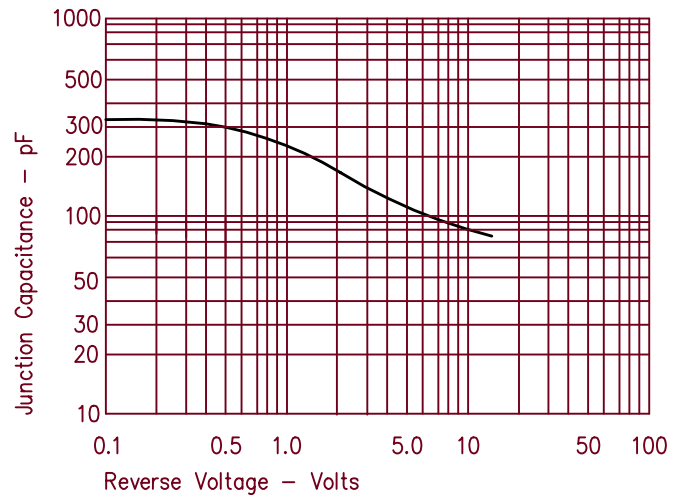


Figure 2  
Typical Reverse Characteristics

